

# The 11<sup>th</sup> European Conference on Silicon Carbide & Related Materials (ECSCRM2016)

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The 11<sup>th</sup> European Conference on Silicon Carbide & Related Materials (ECSCRM2016) is an important international forum that brings together world leading specialist working in different areas of wide bandgap semiconductors. More than 250 contributed papers, 18 plenary and invited talks presented as oral and poster presentations. This year the conference was held at Porto Carras Resort, Halkidiki, Greece.

I participated in poster presentation with two posters:

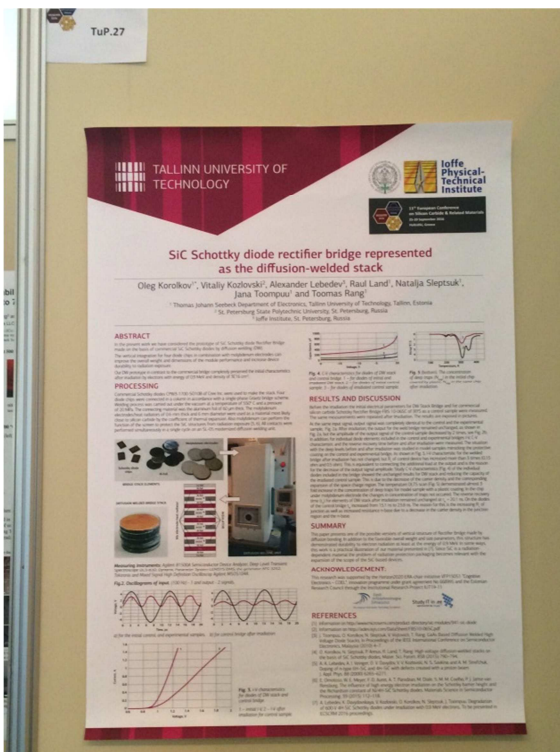
**1. SiC Schottky Diode Rectifier Bridge Represented as the Diffusion Welded Stack**

The poster considered prototype of SiC Schottky diode Rectifier Bridge on the basis of commercial SiC Schottky diodes by diffusion welding. The bridge vertical integration can improve the overall weight, dimensions of the module performance and device durability to radiation exposure.

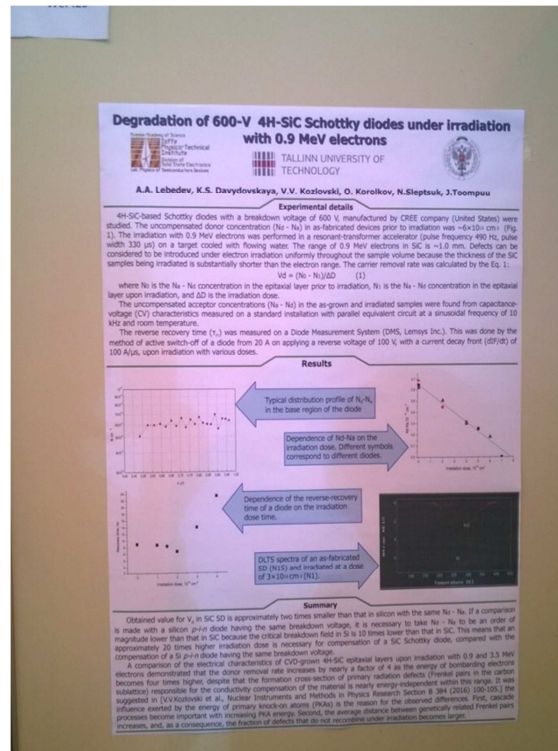
**2. Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9MeV electrons**

The second poster presents the obtained measurements by DLTS method on 600-V 4H-SiC Schottky diodes before and after irradiation.

Full papers of ECSCRM2016 conference will be published by Trans Tech Publication Co. in the Materials Science Forum journal (broadly indexed by all the major services). The Estonian Research Portal classificate the ECSCRM2016 conference as 1.1.



**SiC Schottky Diode Rectifier Bridge Represented as the Diffusion Welded Stack**



**Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9MeV elctrcons**



**„Olympic Hall“ the conference ECSCRM2016 venue**